

CDCDB400 PCIe Gen 1~Gen 6 向け DB800ZL 準拠 4 出力クロック・バッファ

1 特長

- 4 つの LP-HCSL 出力、プログラム可能な内蔵 85Ω (デフォルト) または 100Ω 差動出力終端付き
- 4 つのハードウェア出力イネーブル (OE#) 制御
- PCIe Gen 6 フィルタ後の付加位相ジッタ : 20fs RMS (最大値)
- PCIe Gen 5 フィルタ後の付加位相ジッタ : 25fs RMS (最大値)
- DB2000Q フィルタ後の付加位相ジッタ : 38fs RMS (最大値)
- 共通クロック (CC) アーキテクチャと個別リファレンス (IR) アーキテクチャをサポート
 - スペクトラム拡散対応
- 出力間スキュー : <50ps
- 入出力間遅延 : <3ns
- フェイルセーフ入力
- プログラマブルな出力スルーレート制御機能
- 3 つの選択可能な SMBus アドレス
- コアおよび入出力電源電圧 : 3.3V
- ハードウェア制御による低消費電力モード (PD#)
- 消費電流 : 46mA (最大値)
- 5mm × 5mm、32 ピン VQFN パッケージ

2 アプリケーション

- マイクロサーバー / タワー・サーバー
- ストレージ・エリア・ネットワーク (SAN) および
ホスト・バス・アダプタ (HBA) カード
- ネットワーク接続ストレージ (NAS)
- ハードウェア・アクセラレータ
- ラック・サーバー
- 通信スイッチ
- モジュール搭載コンピュータ
- CT および PET スキャナ
- 高耐久性 PC とラップトップ

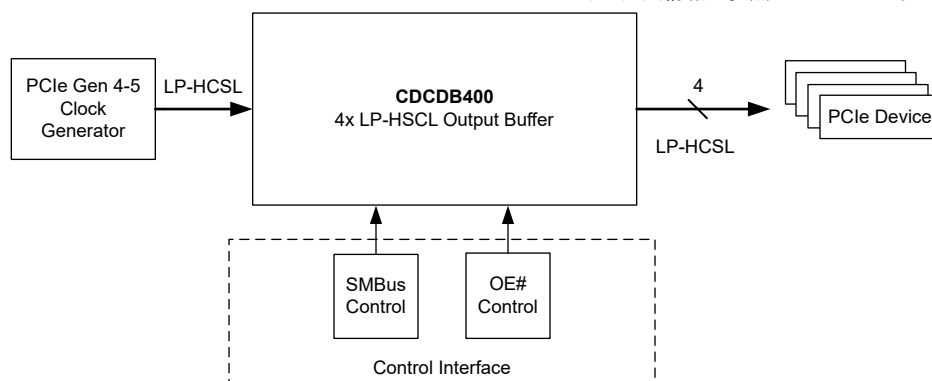
3 説明

CDCDB400 は、PCIe Gen 1 ~ 6、QuickPath Interconnect (QPI)、UPI、SAS、SATA インターフェイス用のリファレンス・クロックを分配できる 4 出力 LP-HCSL、DB800ZL 準拠クロック・バッファです。SMBus インターフェイスおよび 4 本の出力イネーブル・ピンにより、4 個の出力すべてを個別に設定および制御できます。CDCDB400 は DB800ZL から派生したバッファであり、DB800ZL 仕様のシステム・パラメータと同等またはそれを上回る性能を備えています。このデバイスは、DB2000Q 仕様のパラメータと同等またはそれを上回る性能も備えています。CDCDB400 は、5mm × 5mm の 32 ピン VQFN パッケージで供給されます。

製品情報

部品番号	パッケージ (1)	本体サイズ (公称)
CDCDB400	VQFN (32)	5.00mm × 5.00mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



CDCDB400 システム図



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (November 2021) to Revision A (May 2022)	Page
• データシートのタイトルを更新.....	1
• データシートに PCIe Gen 6 を追加.....	1
• Changed the pin description for pin 5.....	3

5 Pin Configuration and Functions

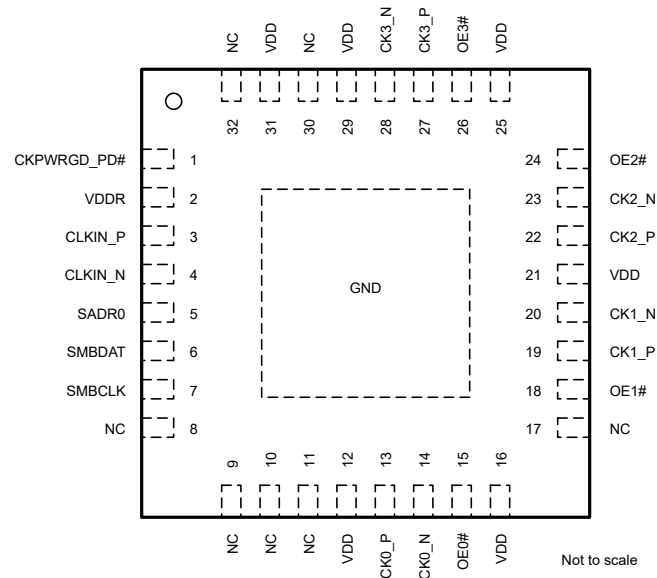


图 5-1. CDCDB400 RHB Package 32-Pin VQFN Top View

表 5-1. Pin Functions

PIN		TYPE ⁽²⁾	DESCRIPTION
NAME	NO.		
INPUT CLOCK			
CLKIN_P	3	I	LP-HCSL differential clock input. Typically connected directly to the differential output of clock source.
CLKIN_N	4	I	
OUTPUT CLOCKS			
CK0_P	13	O	LP-HCSL differential clock output of channel 0. Typically connected directly to PCIe differential clock input. If unused, the pins can be left no connect.
CK0_N	14	O	
CK1_P	19	O	LP-HCSL differential clock output of channel 1. Typically connected directly to PCIe differential clock input. If unused, the pins can be left no connect.
CK1_N	20	O	
CK2_P	22	O	LP-HCSL differential clock output of channel 2. Typically connected directly to PCIe differential clock input. If unused, the pins can be left no connect.
CK2_N	23	O	
CK3_P	27	O	LP-HCSL differential clock output of channel 3. Typically connected directly to PCIe differential clock input. If unused, the pins can be left no connect.
CK3_N	28	O	
MANAGEMENT AND CONTROL ⁽¹⁾			
CKPWRGD_PD#	1	I, S, PD	Clock Power Good and Power Down multi-function input pin with internal 180-kΩ pulldown. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. After PWRGD has been asserted high for the first time, the pin becomes a PD# pin and it controls power-down mode: LOW: Power-down mode, all output channels tri-stated. HIGH: Normal operation mode.

表 5-1. Pin Functions (continued)

PIN		TYPE ⁽²⁾	DESCRIPTION
NAME	NO.		
OE0#	15	I, S, PD	Output Enable for channel 0 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 0. HIGH: disable output channel 0.
OE1#	18	I, S, PD	Output Enable for channel 1 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 1. HIGH: disable output channel 1.
OE2#	24	I, S, PD	Output Enable for channel 2 with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 2. HIGH: disable output channel 2.
OE3#	26	I, S, PD	Output Enable for channel 3, with internal 180-kΩ pulldown, active low. Typically connected to GPIO of microcontroller. If unused, the pin can be left no connect. LOW: enable output channel 3. HIGH: disable output channel 3.
SMBUS AND SMBUS ADDRESS			
SADR0	5	I, S, PU / PD	SMBus address strap bit. This is a 3-level input that is decoded in conjunction with pin B8 to set SMBus address. It has internal 180-kΩ pullup / pulldown network biasing to GND when no connect. For a high-level input configuration, the pin should be pulled up to 3.3-V VDD through an external pullup resistor from 1k to 5k with 5% tolerance. For a low-level input configuration input, the pin should be pulled down to ground through an external pulldown resistor from 1k to 5k with 5% tolerance. For a mid-level input configuration, the pin should be left floating and not connected to VDD or ground.
SMBDAT	6	I / O	Data pin of SMBus interface. Typically pulled up to 3.3-V VDD using external pullup resistor. The recommended pullup resistor value is > 8.5k.
SMBCLK	7	I	Clock pin of SMBus interface. Typically pulled up to 3.3-V VDD using external pullup resistor. The recommended pullup resistor value is > 8.5k.
SUPPLY VOLTAGE AND GROUND			
VDDR	2	P	Power supply input for input clock receiver. Connect to 3.3-V power supply rail with decoupling capacitor to GND. Place a 0.1-μF capacitor close to each supply pin between power supply and ground.
VDD	12, 16, 21, 25, 29, 31	P	3.3-V power supply for output channels and core voltage.
GND	DAP	G	Ground. Connect ground pad to system ground.
NO CONNECT			
NC	8, 9, 10, 11, 17, 30	—	Do not connect pins to GND or VDD. Leave floating.
NC	32	—	Pin may be connected to GND, VDD, or otherwise tied to any potential within the Supply Voltage range stated in the Absolute Maximum Ratings.

(1) The “#” symbol at the end of a pin name indicates that the active state occurs when the signal is at a low voltage level. When “#” is not present, the signal is active high.

(2) The definitions below define the I/O type for each pin.

- I = Input
- O = Output
- I / O = Input / Output
- PU / PD = Internal 180-kΩ Pullup / Pulldown network biasing to VDD/2
- PD = Internal 180-kΩ Pulldown
- S = Hardware Configuration Pin
- P = Power Supply
- G = Ground

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{DD} , V _{DD_R}	Power supply voltage	-0.3	3.6	V
V _{IN}	IO input voltage	-0.3	3.6	V
T _J	Junction temperature		125	°C
T _{stg}	Storage temperature	-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±3500	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002, all pins ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	IO, Core supply voltage	3	3.3	3.6	V
V _{DD_R}	Input supply voltage	3	3.3	3.6	V
T _A	Ambient temperature	-40		105	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		CDCDB400		UNIT
		RHB (QFN)		
		32 PINS		
R _{θJA}	Junction-to-ambient thermal resistance	35.3		°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	27.3		°C/W
R _{θJB}	Junction-to-board thermal resistance	16.2		°C/W
Ψ _{JT}	Junction-to-top characterization parameter	0.6		°C/W
Ψ _{JB}	Junction-to-board characterization parameter	16.2		°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	6.1		°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

VDD, VDD_R = 3.3 V ± 5 %, -40°C ≤ T_A ≤ 85°C. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONSUMPTION						
I _{DD_R}	Core supply current	Active mode. CKPWRGD_PD# = 1			8.5	mA
		Power-down mode. CKPWRGD_PD# = 0			2	
I _{DD}	IO supply current	All outputs disabled			18	mA
		All outputs active, 100 MHz (per output)			8.5	
		Power-down mode. CKPWRGD_PD# = 0			1.5	
CLOCK INPUT						
f _{IN}	Input frequency		50	100	250	MHz
V _{IN}	Input voltage swing	Differential voltage between CLKIN_P and CLKIN_N ⁽¹⁾	200		2300	mV _{Diff-peak}
dV/dt	Input voltage edge rate	20% - 80% of input swing	0.7			V/ns
DV _{CROSS}	Total variation of V _{CROSS}	Total variation across V _{CROSS}		140		mV
DC _{IN}	Input duty cycle		40		60	%
C _{IN}	Input capacitance ⁽²⁾	Differential capacitance between CLKIN_P and CLKIN_N pins		2.2		pF
CLOCK OUTPUT						
f _{OUT}	Output frequency		50	100	250	MHz
C _{OUT}	Output capacitance ⁽¹⁾	Differential capacitance between CKx_P and CKx_N pins		4		pF
V _{OH}	Output high voltage	Single-ended ^{(2) (3)}	225		270	mV
V _{OL}	Output low voltage		10		150	
V _{HIGH}	Output high voltage	Measured into an AC load as defined in DB800ZL	660		850	
V _{LOW}	Output low voltage	Measured into an AC load as defined in DB800ZL	-150		150	
V _{MAX}	Output Max voltage	Measured into an AC load as defined in DB800ZL			1150	
V _{CROSS}	Crossing point voltage	See ^{(3) (4)}	130		200	
V _{CROSSAC}	Crossing point voltage (AC load)	Measured into an AC load as defined in DB800ZL	250		550	
DV _{CROSS}	Total variation of V _{CROSS}	Variation of V _{CROSS} ^{(3) (4)}		35	140	
V _{ovs}	Overshoot voltage	See ⁽³⁾			V _{OH} +75	
V _{ovs(AC)}	Overshoot voltage (AC load)	Measured into an AC load as defined in DB800ZL			V _{HIGH} +30 0	
V _{uds}	Undershoot voltage	See ⁽³⁾			V _{OL} -75	
V _{uds(AC)}	Undershoot voltage	Measured into an AC load as defined in DB800ZL			V _{LOW} - 300	
V _{rb}	Ringback Voltage	Measured into an AC load as defined in DB800ZL and taken from single-ended waveform.				V
		Measured into an AC load as defined in DB800ZL and taken from single-ended waveform.	-0.2		0.2	

VDD, VDD_R = 3.3 V ± 5 %, -40°C ≤ T_A ≤ 85°C. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
Z _{DIFF}	Differential impedance (Default setting, 85 Ω)	Measured at V _{OL} /V _{OH}		81	85	89	Ω
	Differential impedance (Output impedance selection bit = 1, 100 Ω)	Measured at V _{OL} /V _{OH}		95	100	105	
Z _{DIFF_CROSS}	Differential impedance (Default setting, 85 Ω)	Measured at V _{CROSS}		68	85	102	
	Differential impedance (Output impedance selection bit = 1, 100 Ω)	Measured at V _{CROSS}		80	100	120	
t _{EDGE}	Differential edge rate	Measured (±150 mV) around V _{CROSS} ⁽⁷⁾		2		4	V/ns
Dt _{EDGE}	Edge rate matching	Measured (±150 mV) V _{CROSS} ⁽⁷⁾				20	%
t _{STABLE}	Power good assertion to stable clock output	CKPWRGD_PD# pin transitions from 0 to 1, f _{IN} = 100 MHz	Measured when positive output reaches 0.2 V			1.8	ms
t _{DRIVE_PD#}	Power good assertion to outputs driven high	CKPWRGD_PD# pin transitions from 0 to 1, f _{IN} = 100 MHz	Measured when positive output reaches 0.2 V			300	μs
t _{OE}	Output enable assertion to stable clock output	OEx# pin transitions from 1 to 0				10	CLKIN Periods
t _{OD}	Output enable de-assertion to no clock output	OEx# pin transitions from 0 to 1				10	
t _{PD}	Power-down assertion to no clock output	CKPWRGD_PD# pin transitions from 1 to 0				3	
t _{DCD}	Duty cycle distortion	Differential; f _{IN} = 100 MHz, f _{IN_DC} = 50%		-1		1	%
t _{DLY}	Propagation delay	See ⁽⁵⁾		0.5		3	ns
t _{SKEW}	Skew between outputs	See ⁽⁶⁾				50	ps
t _{DELAY(IN-OUT)}	Input to output delay variation	Input-to-output delay variation at 100 MHz across voltage and temperature		-250		250	ps
J _{CKX_PCIE} ⁽⁷⁾	Additive jitter for DB2000QL	DB2000QL filter, for input of 200-mV differential swing at 1.5 V/ns				0.038	ps, RMS
	Additive jitter for PCIe6.0	PLL BW: 0.5 - 1 MHz; CDR = 10 MHz	Input clock slew rate = 2 V/ns			0.02	
	Additive jitter for PCIe5.0	PCIe5.0 filter				0.025	
	Additive jitter for PCIe4.0	PLL BW = 2 - 5 MHz; CDR = 10 MHz	Input clock slew rate ≥ 1.8 V/ns			0.06	
	Additive jitter for PCIe3.0		Input clock slew rate ≥ 0.6 V/ns			0.1	
J _{CKX}	Additive jitter	f _{IN} = 100 MHz; slew rate ≥ 3 V/ns; 12 kHz to 20 MHz integration bandwidth.			100	160	fs, RMS
NF	Noise floor	f _{IN} = 100 MHz; f _{Offset} ≥ 10 MHz	Input clock slew rate ≥ 3 V/ns		-160	-155	dBc/Hz
SMBUS INTERFACE, OEx#, CKPWRGD_PD#							
V _{IH}	High level input voltage			2.0			V
V _{IL}	Low level input voltage					0.8	
I _{IH}	Input leakage current	With internal pullup/pulldown	GND ≤ V _{IN} ≤ V _{DD}	-30		30	μA

VDD, VDD_R = 3.3 V ± 5 %, -40°C ≤ T_A ≤ 85°C. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I _{IL}	Input leakage current	With internal pullup/pulldown	GND ≤ V _{IN} ≤ V _{DD}	-30		30	μA
I _{IH}	Input leakage current	Without internal pullup/pulldown	GND ≤ V _{IN} ≤ V _{DD}	-5		5	μA
I _{IL}	Input leakage current	Without internal pullup/pulldown	GND ≤ V _{IN} ≤ V _{DD}	-5		5	μA
C _{IN}	Input capacitance				4.5		pF
C _{OUT}	Output capacitance				4.5		pF
3-LEVEL DIGITAL INTERFACE (SADR0)							
V _{IH}	High level input voltage			2.3			V
V _{IM}	Mid level input voltage			1.25	V _{DD} /2	1.725	
V _{IL}	Low level input voltage					0.85	
I _{IH}	Input leakage current	With internal pullup/pulldown	V _{IN} = V _{DD}	-30		30	μA
I _{IL}	Input leakage current	With internal pullup/pulldown	V _{IN} = GND	-30		30	μA
C _{IN}	Input capacitance ⁽¹⁾				4.5		pF

- (1) Voltage swing includes overshoot.
- (2) Not tested in production. Ensured by design and characterization.
- (3) Measured into DC test load.
- (4) V_{CROSS} is single-ended voltage when CKx_P = CKx_N with respect to system ground. Only valid on rising edge of CKx, when CKx_P is rising.
- (5) Measured from rising edge of CLK_IN to any CKx output.
- (6) Measured from rising edge of any CKx output to any other CKx output.
- (7) Measured into AC test load.

6.6 Timing Requirements

VDD, VDD_R = 3.3 V ± 5 %, -40°C ≤ T_A ≤ 85°C. Typical values are at VDD = VDD_R = 3.3 V, 25°C (unless otherwise noted)

			MIN	NOM	MAX	UNIT
SMBUS COMPATIBLE INTERFACE TIMING						
f _{SMB}	SMBus operating frequency		10		400	kHz
t _{BUF}	Bus free time between STOP and START		4.7			μs
t _{HD_STA}	START condition hold time	SMBCLK low after SMBDAT low	4			
t _{SU_STA}	START condition setup time	SMBCLK high before SMBDAT low	4.7			
t _{SU_STO}	STOP condition setup time		4			
t _{HD_DAT}	SMBDAT hold time		300			ns
t _{SU_DAT}	SMBDAT setup time		250			
t _{TIMEOUT}	Detect SMBCLK low timeout	In terms of device input clock frequency	1e6			cycles
t _{LOW}	SMBCLK low period		4.7			μs
t _{HIGH}	SMBCLK high period		4		50	
t _F	SMBCLK/SMBDAT fall time ⁽¹⁾				300	ns
t _R	SMBCLK/SMBDAT rise time ⁽²⁾				1000	

- (1) TF = (VIHMIN + 0.15) to (VILMAX - 0.15)
- (2) TR = (VILMAX - 0.15) to (VIHMIN + 0.15)

6.7 Typical Characteristics

Figure 6-1 shows both the phase noise of the source as well as the output of the DUT (CDCDB400). It can be seen from the phase noise plot that the DUT has a very low phase noise profile with total jitter of 81.5 fs, rms. If we rms subtract the clock reference noise, the additive jitter of CDCDB400 under typical conditions would be lower than 81.5 fs, rms.

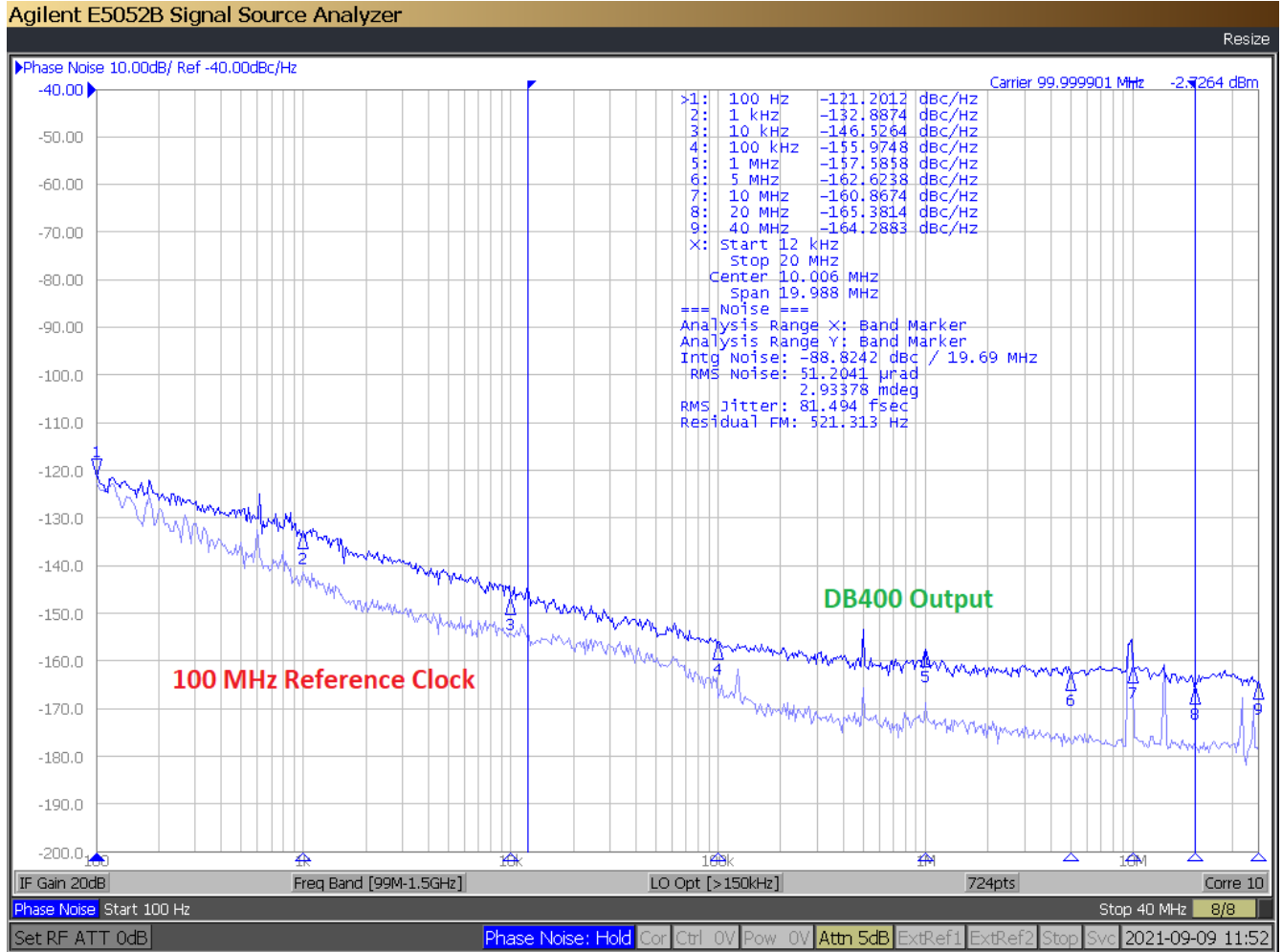
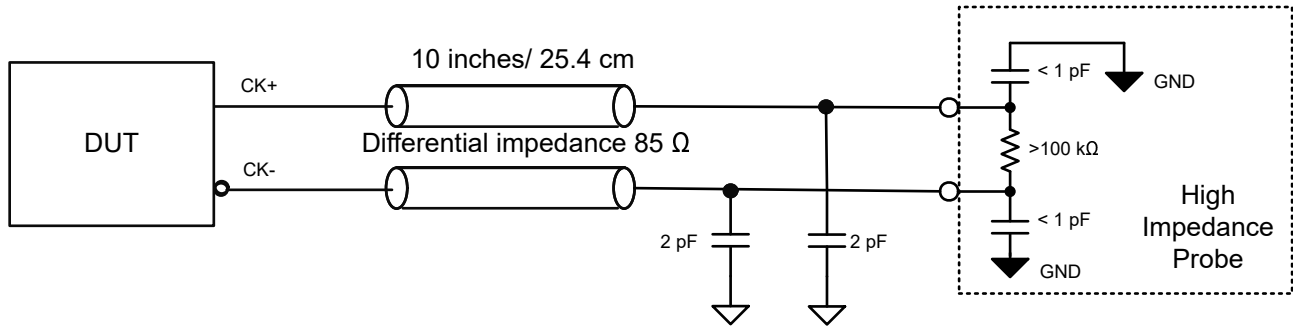
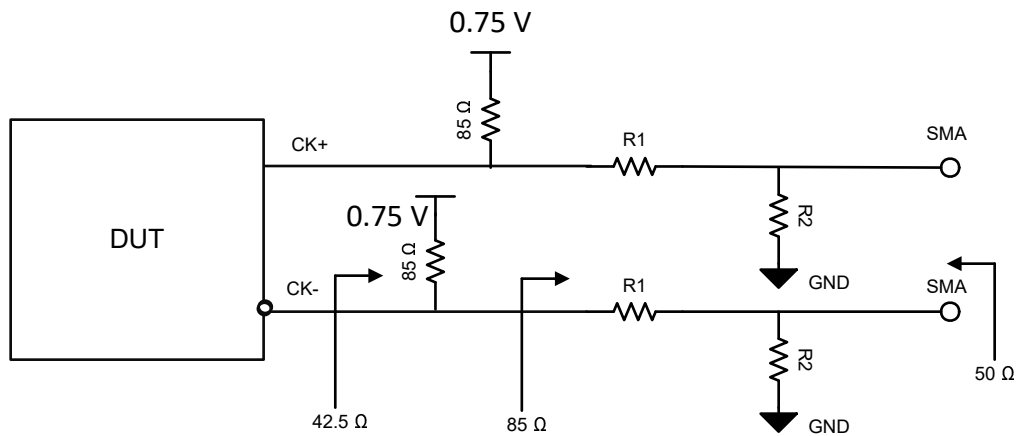


Figure 6-1. CDCDB400 Clock Out (CK0:4) Phase Noise

7 Parameter Measurement Information



☒ 7-1. AC Test Load (Referencing Intel DB2000QL Document)



R1 = 47 Ω and R2 = 147 Ω.

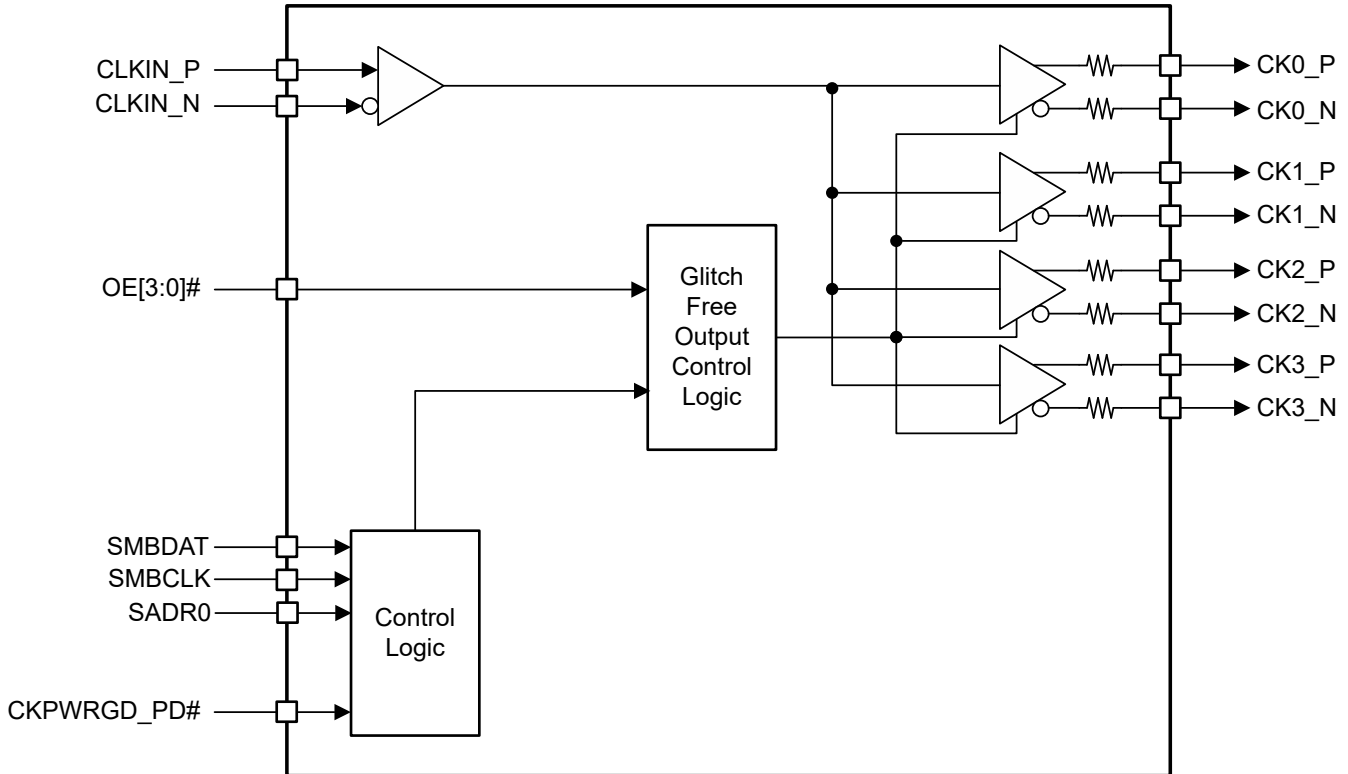
☒ 7-2. DC Simulation Load (Referencing Intel DB2000QL Document)

8 Detailed Description

8.1 Overview

The CDCDB400 is a low additive-jitter, low propagation delay clock buffer designed to meet the strict performance requirements for PCIe Gen 1-6, QPI, UPI, SAS, and SATA reference clocks in CC, SRNS, or SRIS architectures. The CDCDB400 allows buffering and replication of a single clock source to up to four individual outputs in the LP-HCSL format. The CDCDB400 also includes status and control registers accessible by an SMBus version 2.0 compliant interface. The device integrates a large amount of external passive components to reduce overall system cost.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Fail-Safe Input

The CDCDB400 is designed to support fail-safe input operation feature. This feature allows the user to drive the device inputs before V_{DD} is applied without damaging the device. Refer to the [Absolute Maximum Ratings](#) table for more information on the maximum input supported by the device.

8.3.2 Output Enable Control

The CDCDB400 uses SMBus and $OE\#$ to control the state of the output channels. The $OE\#$ pins control the state of the output with the same number. For example, the $OE3\#$ pin controls the state of the CK3 output driver. The SMBus registers may enable or disable the output when the corresponding $OE\#$ pin is held low.

8.3.3 SMBus

The CDCDB400 has an SMBus interface that is active only when $CKPWRGD_PD\# = 1$. The SMBus allows individual enable/disable of each output.

When $CKPWRGD_PD\# = 0$, the SMBus pins are placed in a Hi-Z state, but all register settings are retained. The SMBus register values are only retained while V_{DD} remains inside of the recommended operating voltage.

8.3.3.1 SMBus Address Assignment

The SMBus address is assigned by configuring the SADR0 pin which is capable of supporting three levels. This configuration allows the CDCDB400 to assume three different SMBus addresses.

The SMBus address pin is sampled when PWRGD is set to 1. See 表 8-1 for address pin configuration. The address can only be changed by power cycling the device.

表 8-1. SMBus Address Assignment

SADR0	SMBus ADDRESS : WRITE OPERATION (READ/WRITE=0)	SMBus ADDRESS : READ OPERATION (READ/WRITE=1)
L	0xD8	0xD9
M	0xDA	0xDB
H	0xDE	0xDF

8.4 Device Functional Modes

8.4.1 CKPWRGD_PD# Function

The CKPWRGD_PD# pin is used to set two state variables inside of the device: PWRGD and PD#. The PWRGD and PD# variables control which functions of the device are active at any time, as well as the state of the input and output pins.

The PWRGD and PD# states are multiplexed on the CKPWRGD_PD# pin. CKPWRGD_PD# must remain below V_{OL} and not exceed $V_{DDR} + 0.3\text{ V}$ until V_{DD} and V_{DDR} are present and within the recommended operating conditions. After CKPWRGD_PD# is set high, a valid CLKIN must be present to use PD#.

The first rising edge of the CKPWRGD_PD# pin sets PWRGD = 1. After PWRGD is set to 1, the CKPWRGD_PD# pin is used to assert PD# mode only. PWRGD variable will only be cleared to 0 with the removal of V_{DD} and V_{DDR} .

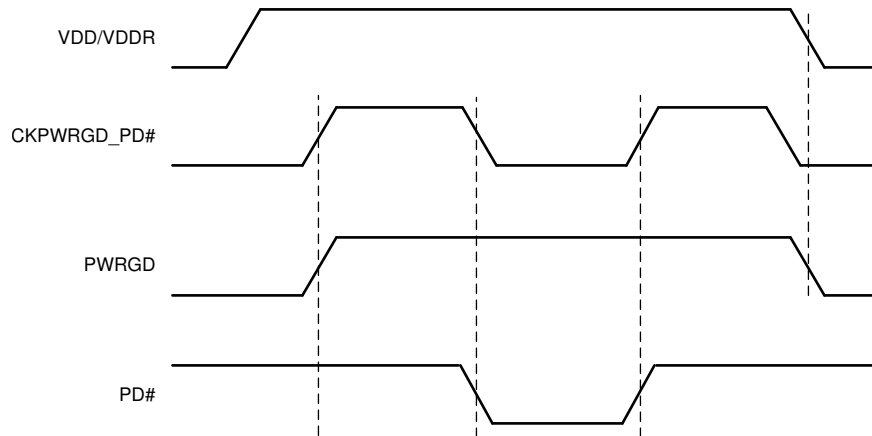


图 8-1. PWRGD and PD# State Changes

8.4.2 OE[3:0]# and SMBus Output Enables

Each output channel, 0 to 3, can be individually enabled or disabled by a SMBus control register bit, called SMB enable bits. Additionally, each output channel has a dedicated, corresponding, OE[3:0]# hardware pin. The OE[3:0]# pins are asynchronously asserted-low signals that may enable or disable the output.

Refer to 表 8-2 for enabling and disabling outputs through the hardware and software. Note that both the SMB enable bit must be a 1 and the OEx# pin must be an input low voltage 0 for the output channel to be active.

表 8-2. OE[3:0]# Functionality

Control Inputs	Power State Variables (Internal)		CLKIN	OE[3:0]# HARDWARE PINS AND SMBus CONTROL REGISTER BITS			CK[3:0]_P/ CK[3:0]_N
	CKPWRGD_PD#	PWRGD		PD#	OE[3:0]#	OUT_EN_CLK[3:0]	
0	0	0	X	X	X	X	LOW/LOW
1	1	1	X ⁽¹⁾	X	0	0	LOW/LOW
						1	TRI-STATE
				1	X	0	LOW/LOW
					1	TRI-STATE	
		Running ⁽¹⁾	0	1	X	Running	
0		0	X ⁽²⁾	X	X	0	LOW/LOW
						1	TRI-STATE

(1) To enter the power-down state, CLKIN must remain active for at least 3 clock cycles after CKPWRGD_PD# transitions from 1 to 0.

(2) To enter the powered-up state with active clock outputs, CLKIN must be active before CKPWRGD_PD# transitions from 0 to 1.

8.4.3 Output Slew Rate Control

The CDCDB400 provides output slew rate control feature which customer can use to compensate for increased output trace length based on their board design. The slew rate of the 4 outputs, CK0 to CK3, can be changed within a given range by a SMBus control register called CAPTRIM. Refer to 表 8-16 for more information.

8.4.4 Output Impedance Control

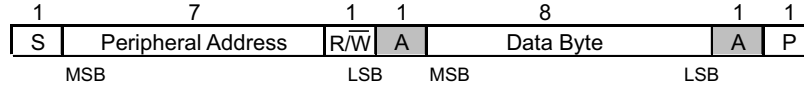
The integrated termination on the CDCDB400 can be programmed either for 85 Ω or 100 Ω. This flexibility ensures that the customer can use the same device across various applications irrespective of the characteristic board impedance which is typically either 85 Ω or 100 Ω. This termination resistor can be changed for all the outputs as whole using bit 5 of a register called OUTSET. Refer to 表 8-14 for more information.

8.5 Programming

The CDCDB400 uses SMBus to program the states of its four output drivers. See [SMBus](#) for more information on the SMBus programming, and [Register Maps](#) for information on the registers.

表 8-3. Command Code Definition

BIT	DESCRIPTION
7	0 = <i>Block Read</i> or <i>Block Write</i> operation 1 = <i>Byte Read</i> or <i>Byte Write</i> operation
(6:0)	Register address for <i>Byte</i> operations, or starting register address for <i>Block</i> , operations



- S Start Condition
- Sr Repeated Start Condition
- R/W 1 = Read (Rd); 0 = Write (Wr)
- A Acknowledge (ACK = 0 and NACK = 1)
- P Stop Condition
- Controller-to-Peripheral Transmission
- Peripheral-to-Controller Transmission

图 8-2. Generic Programming Sequence

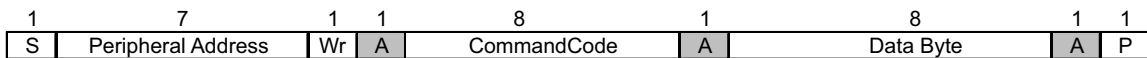


图 8-3. Byte Write Protocol

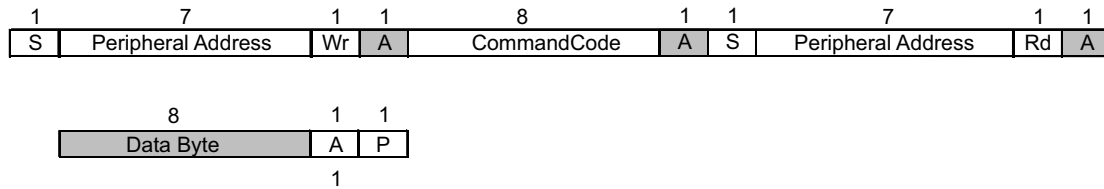


图 8-4. Byte Read Protocol

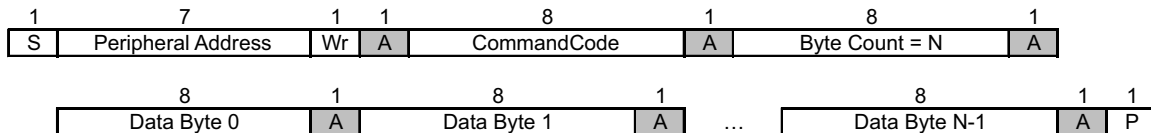


图 8-5. Block Write Protocol

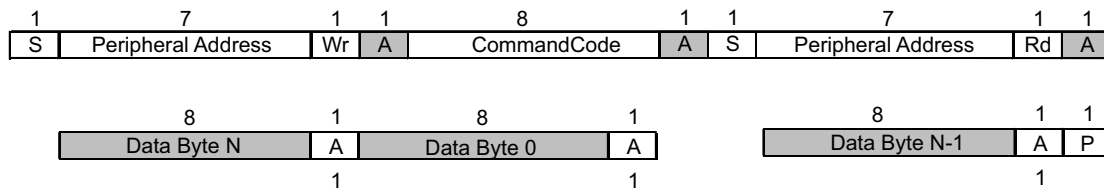


图 8-6. Block Read Protocol

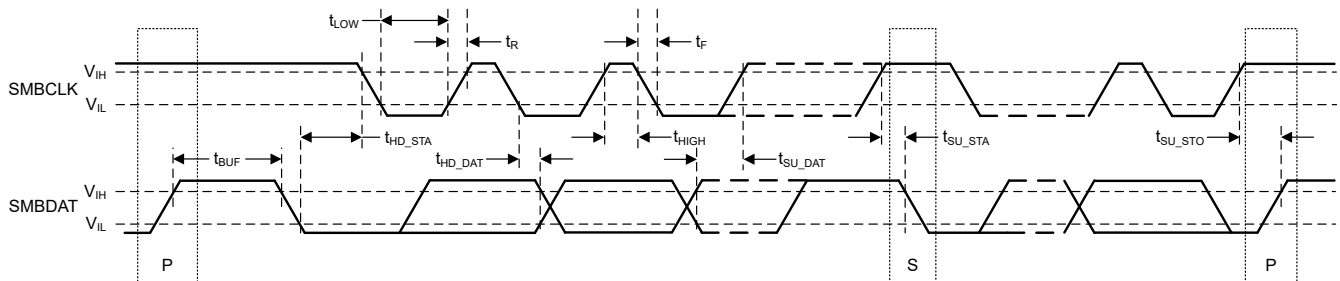


图 8-7. SMBus Timing Diagram

8.6 Register Maps

8.6.1 CDCDB400 Registers

表 8-4 lists the CDCDB400 registers. All register locations not listed in 表 8-4 should be considered as reserved locations and the register contents should not be modified.

表 8-4. CDCDB400 Registers

Address	Acronym	Register Name	Section
0h	RCR1	Reserved Control Register 1	Go
1h	OECR1	Output Enable Control 1	Go
2h	OECR2	Output Enable Control 2	Go
3h	OERDBK	Output Enable# Pin Read Back	Go
4h	RCR2	Reserved Control Register 2	Go
5h	VDRREVID	Vendor/Revision Identification	Go
6h	DEVID	Device Identification	Go
7h	BTRDCNT	Byte Read Count Control	Go
8h	OUTSET	Output Setting Control	Go
4Ch	CAPTRIM	Slew Rate Capacitor Cluster 1 & 2	Go

Complex bit access types are encoded to fit into small table cells. 表 8-5 shows the codes that are used for access types in this section.

表 8-5. CDCDB400 Access Type Codes

Access Type	Code	Description
Read Type		
R	R	Read
Write Type		
W	W	Write
Reset or Default Value		
-n		Value after reset or the default value

8.6.1.1 RCR1 Register (Address = 0h) [reset = 47h]

RCR1 is shown in 表 8-6.

Return to the [Summary Table](#).

The RCR1 register contains reserved bits.

表 8-6. RCR1 Register Field Descriptions

Bit	Field	Type	Reset	Description
7-4	Reserved	R	4h	Reserved.
3-0	Reserved	R/W	7h	Writing to these bits will not affect the functionality of the device.

8.6.1.2 OECR1 Register (Address = 1h) [reset = FFh]

OECR1 is shown in 表 8-7.

Return to the [Summary Table](#).

The OECR1 register contains bits that enable or disable individual output clock channels [1:0].

表 8-7. OECR1 Register Field Descriptions

Bit	Field	Type	Reset	Description
7	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
6	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
5	OUT_EN_CLK1	R/W	1h	This bit controls the output enable signal for output channel CK1_P/ CK1_N. 0h = Output Disabled 1h = Output Enabled
4	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
3	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
2	OUT_EN_CLK0	R/W	1h	This bit controls the output enable signal for output channel CK0_P/ CK0_N. 0h = Output Disabled 1h = Output Enabled
1	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
0	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.

8.6.1.3 OECR2 Register (Address = 2h) [reset = 0Fh]

OECR2 is shown in [表 8-8](#).

Return to the [Summary Table](#).

The OECR2 register contains bits that enable or disable individual output clock channels [3:2].

表 8-8. OECR2 Register Field Descriptions

Bit	Field	Type	Reset	Description
7-4	Reserved	R/W	0h	Writing to these bits will not affect the functionality of the device.
3	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
2	OUT_EN_CLK3	R/W	1h	This bit controls the output enable signal for output channel CK3_P/ CK3_N. 0h = Output Disabled 1h = Output Enabled
1	Reserved	R/W	1h	Writing to this bit will not affect the functionality of the device.
0	OUT_EN_CLK2	R/W	1h	This bit controls the output enable signal for output channel CK2_P/ CK2_N. 0h = Output Disabled 1h = Output Enabled

8.6.1.4 OERDBK Register (Address = 3h) [reset = 0h]

OERDBK is shown in [表 8-9](#).

Return to the [Summary Table](#).

The OERDBK register contains bits that report the current state of the OE[3:0]# input pins.

表 8-9. OERDBK Register Field Descriptions

Bit	Field	Type	Reset	Description
7	RB_OEZ3	R	0h	This bit reports the logic level present on the OE3# pin.
6	RB_OEZ2	R	0h	This bit reports the logic level present on the OE2# pin.
5-4	Reserved	R	0h	Reserved.
3	RB_OEZ1	R	0h	This bit reports the logic level present on the OE1# pin.
2	Reserved	R	0h	Reserved.

表 8-9. OERDBK Register Field Descriptions (continued)

Bit	Field	Type	Reset	Description
1	RB_OEZ0	R	0h	This bit reports the logic level present on the OE0# pin.
0	Reserved	R	0h	Reserved.

8.6.1.5 RCR2 Register (Address = 4h) [reset = 0h]

RCR2 is shown in [表 8-10](#).

Return to the [Summary Table](#).

The RCR2 register contains reserved bits.

表 8-10. RCR2 Register Field Descriptions

Bit	Field	Type	Reset	Description
7-0	Reserved	R	0h	Reserved.

8.6.1.6 VDRREVID Register (Address = 5h) [reset = 0Ah]

VDRREVID is shown in [表 8-11](#).

Return to the [Summary Table](#).

The VDRREVID register contains a vendor identification code and silicon revision code.

表 8-11. VDRREVID Register Field Descriptions

Bit	Field	Type	Reset	Description
7-4	REV_ID	R	0h	Silicon revision code. Silicon revision code bits [3:0] map to register bits [7:4] directly.
3-0	VENDOR_ID	R	Ah	Vendor identification code. Vendor ID bits [3:0] map to register bits [3:0] directly.

8.6.1.7 DEVID Register (Address = 6h) [reset = E7h]

DEVID is shown in [表 8-12](#).

Return to the [Summary Table](#).

The DEVID register contains a device identification code.

表 8-12. DEVID Register Field Descriptions

Bit	Field	Type	Reset	Description
7-0	DEV_ID	R	E7h	Device ID code. Device ID bits[7:0] map to register bits[7:0] directly.

8.6.1.8 BTRDCNT Register (Address = 7h) [reset = 8h]

BTRDCNT is shown in [表 8-13](#).

Return to the [Summary Table](#).

The BTRDCNT register contains bits [4:0] which configure the number of bytes which will be read back.

表 8-13. BTRDCNT Register Field Descriptions

Bit	Field	Type	Reset	Description
7-5	Reserved	R/W	0h	Writing to these bits will not affect the functionality of the device.
4	BYTE_COUNTER	R/W	0h	Writing to this register configures how many bytes will be read back.
3-0	BYTE_COUNTER	R/W	8h	

8.6.1.9 OUTSET Register (Address = 8h) [reset = 0h]

OUTSET is shown in [表 8-14](#).

Return to the [Summary Table](#).

Bit5 of the OUTSET register sets the termination for all the outputs while bit4 can be used to set the power-down state for all outputs. The remaining bits for this register are reserved.

表 8-14. OUTSET Register Field Descriptions

Bit	Field	Type	Reset	Description
7-6	Reserved	R	0h	Reserved.
5	CH_ZOUT_SEL	R/W	0h	Select between 85 Ω (0) and 100 Ω (1) Output impedance
4	d_DRIVE_OP_STATE_CTRL	R/W	0h	Power-down state of all output clocks. 0: LOW/LOW 1: TRI_STATE
3-0	Reserved	R/W	0h	Register bits can be written to 0. Writing a different value than 0 will affect device functionality.

8.6.1.10 CAPTRIM Register (Address = 4Ch) [reset = 66h]

CAPTRIM is shown in [表 8-16](#).

Return to the [Summary Table](#).

Bits [7:4] of the CAPTRIM register is used to control the slew rate for output channel cluster 2. Bits [3:0] control the slew rate for output channel cluster 1. Refer below for cluster identification.

表 8-15. Cluster Identification

Cluster	Outputs
1	CK1, CK0
2	CK3, CK2

表 8-16. CAPTRIM Register Field Descriptions

Bit	Field	Type	Reset	Description
7-4	CLUSTER2_CAP_TRIM	R/W	6h	Slew Rate Reduction Cap Trim for Cluster 2 Default value of 6h. 0: minimum F: maximum
3-0	CLUSTER1_CAP_TRIM	R/W	6h	Slew Rate Reduction Cap Trim for Cluster 1. Default value of 6h. 0: minimum F: maximum

9 Application and Implementation

Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

The CDCDB400 is a fanout buffer that supports PCIe generation 4 and PCIe generation 5 REFCLK distribution. The device is used to distribute up to four copies of a typically 100-MHz clock.

9.2 Typical Application

図 9-1 shows a CDCDB400 typical application. In this application, a clock generator provides a 100-MHz reference to the CDCDB400 which then distributes that clock to PCIe endpoints. The clock generator may be a discrete clock generator like the CDCI6214 or it may be integrated in a larger component such as a Platform Controller Hub (PCH) or application processor.

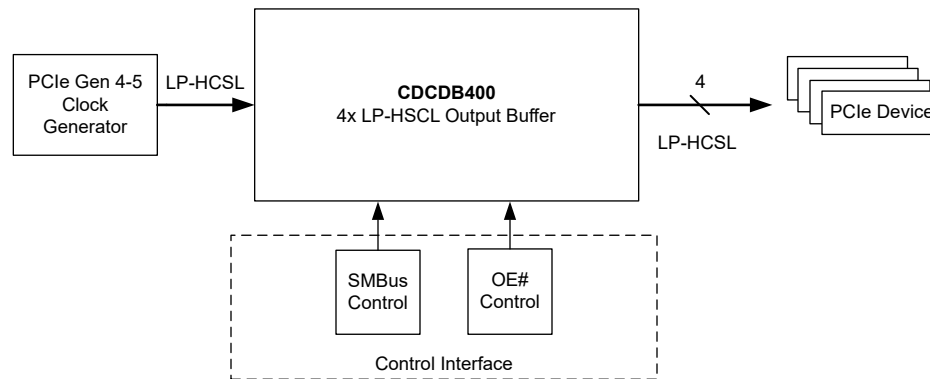


図 9-1. Typical Application

9.2.1 Design Requirements

Consider a typical server motherboard application which must distribute a 100-MHz PCIe reference clock from the PCH of a processor chipset to multiple endpoints. An example of clock input and output requirements is:

- Clock Input:
 - 100-MHz LP-HCSL
- Clock Output:
 - 2x 100-MHz to processors, LP-HCSL
 - 1x 100-MHz to riser/retimer, LP-HCSL
 - 1x 100-MHz to DDR memory controller, LP-HCSL

9.2.2 Detailed Design Procedure

The following items must be determined before starting design of a CDCDB400 socket:

- Output Enable Control Method
- SMBus address

9.2.2.1 Output Enable Control Method

The device provides an option to either use SMBus programmed registers (software) to control the outputs or by using the hardware OE# pins. When using software to control the outputs, the hardware OE# pins can be left floating as each of these pins have a pulldown to ground. Refer to 表 8-2 and [Register Maps](#) for more information on programming the register.

When the user wants to control the outputs with the hardware OE# pins, they can connect these pins to a GPIO controller and set the outputs to HIGH/LOW (see 表 5-1). Registers OECR1 (表 8-7) and OECR2 (表 8-8) show the OUT_EN_CLK3 to OUT_EN_CLK0 bits used to control the outputs. These register bits are set to 1 by default to ensure that the outputs are "software enabled" and their state is therefore set by hardware OE# pins.

9.2.2.2 SMBus Address

Select a SMBus address from the list of potential addresses in 表 8-1. Place the appropriate pullup or pulldown resistor on the SADR0 pin as indicated in the table. Ensure the SMBus address is not already in use to avoid conflict.

9.2.3 Application Curves

图 6-1 in the *Typical Characteristics* section can be used as both an application curve and a typical characteristics plot in this example.

The 图 9-2 and 图 9-3 show characterization data for the Output slew rate for various CAPTRIM codes and across temperature. Customers can use these plots as reference for choosing the appropriate output slew rate based on their system requirement.

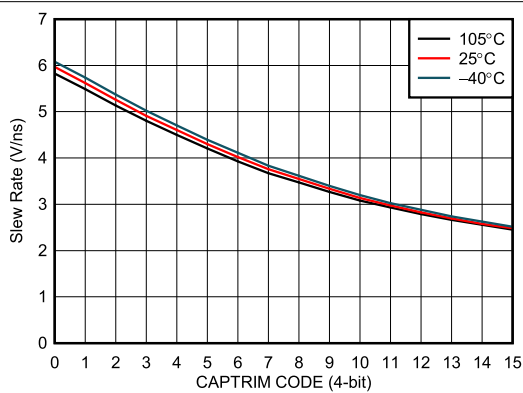


图 9-2. Output Slew Rate vs. CAPTRIM Code

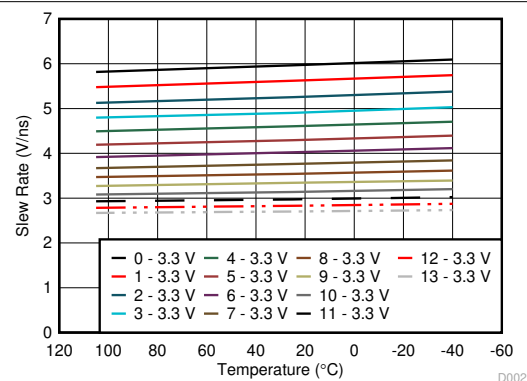


图 9-3. Slew Rate Variation Across Temperature for Different CAPTRIM Code

10 Power Supply Recommendations

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when the jitter and phase noise is critical to applications.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guards the power-supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly use the bypass capacitors, place the capacitors very close to the power-supply terminals and lay out with short loops to minimize inductance. TI recommends to insert a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer. These beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

Figure 10-1 shows the recommended power supply filtering and decoupling method.

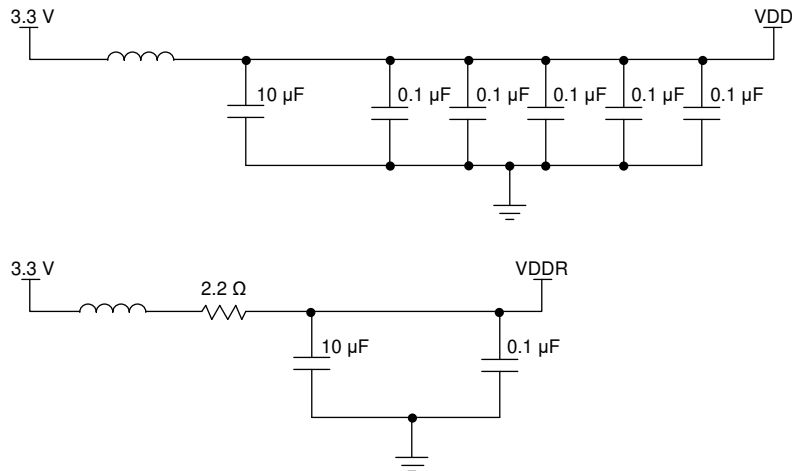


Figure 10-1. Power Supply Decoupling



11 Layout

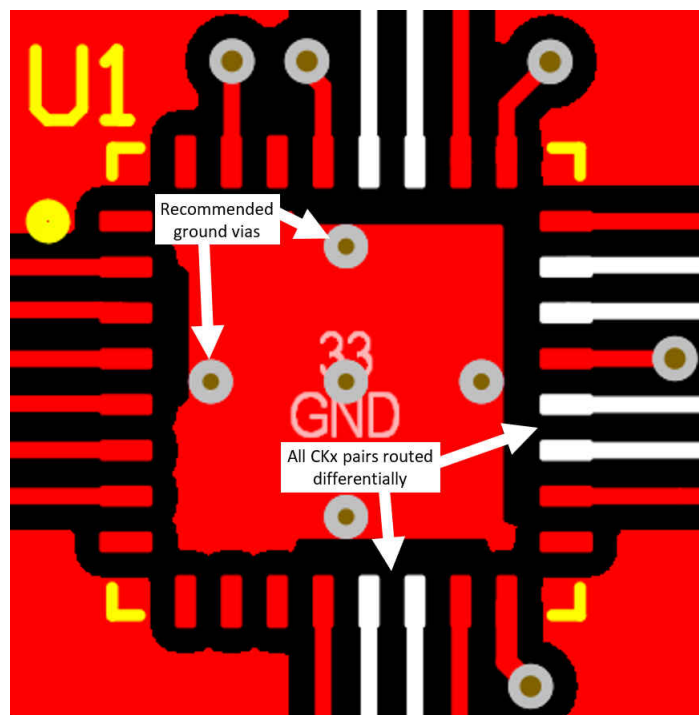
11.1 Layout Guidelines

The following section provides the layout guidelines to ensure good thermal performance and power supply connections for the CDCDB400.

In [Layout Examples](#), the CDCDB400 has 85- Ω differential output impedance LP-HCSL format drivers as per register default settings. All transmission lines connected to CKx pins should be 85- Ω differential impedance, 42.5- Ω single-ended impedance to avoid reflections and increased radiated emissions. If 100- Ω output impedance is enabled, the transmission lines connected to CKx pins should be 100- Ω differential impedance, 50- Ω single-ended impedance. Take care to eliminate or reduce stubs on the transmission lines.

11.2 Layout Examples

 11-1 through  11-3 are printed circuit board (PCB) layout examples that show the application of thermal design practices and a low-inductance ground connection between the device DAP and the PCB.



 11-1. PCB Layout Example for CDCDB400, Top layer

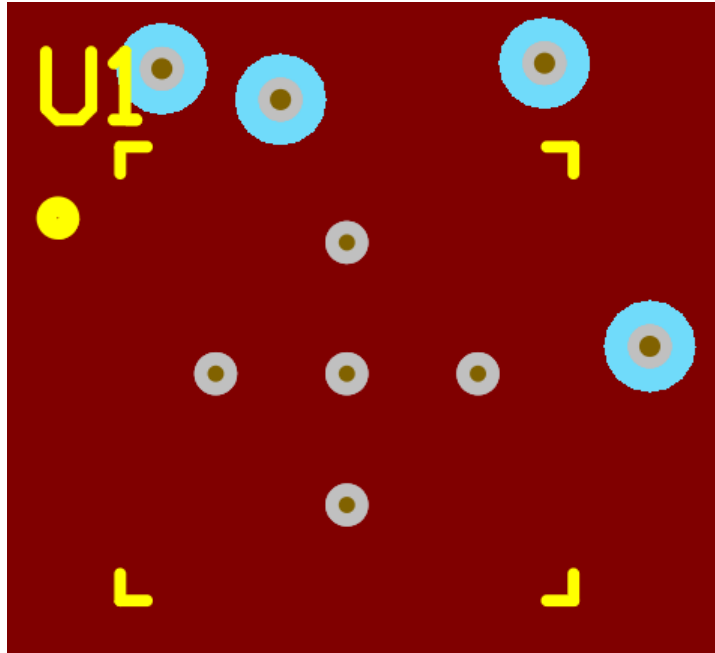


图 11-2. PCB Layout Example for CDCDB400, GND Layer

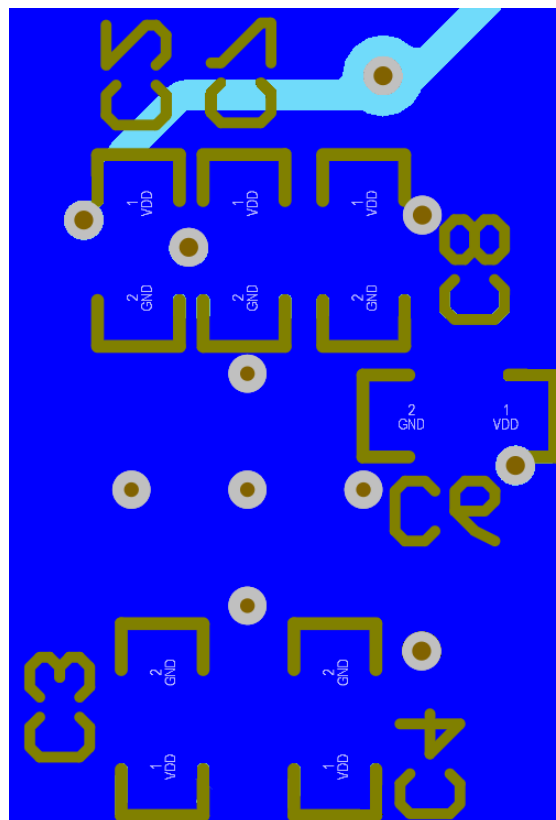


图 11-3. PCB Layout Example for CDCDB400, Bottom Layer

12 Device and Documentation Support

12.1 Device Support

12.1.1 TICS Pro

TICS Pro is an offline software tool for EVM programming and also for register map generation to program a device configuration for a specific application. For TICS Pro, go to <https://www.ti.com/tool/TICSPRO-SW>.

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CDCDB400RHBR	ACTIVE	VQFN	RHB	32	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	CDCB400	Samples
CDCDB400RHBT	ACTIVE	VQFN	RHB	32	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	CDCB400	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCDB400RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.1	8.0	12.0	Q2
CDCDB400RHBT	VQFN	RHB	32	250	180.0	12.4	5.3	5.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCDB400RHBR	VQFN	RHB	32	3000	367.0	367.0	35.0
CDCDB400RHBT	VQFN	RHB	32	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

RHB 32

VQFN - 1 mm max height

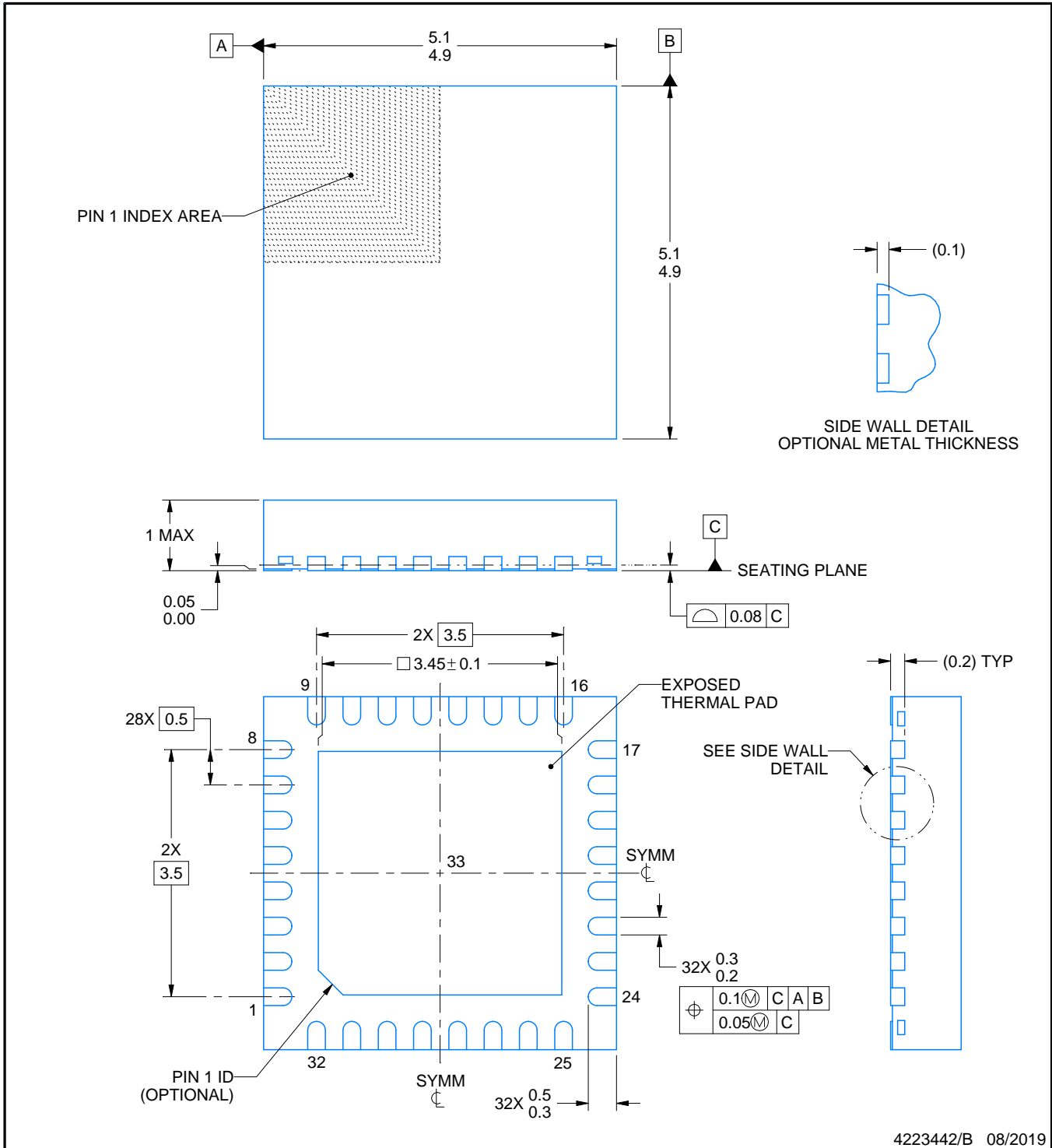
5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224745/A



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NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

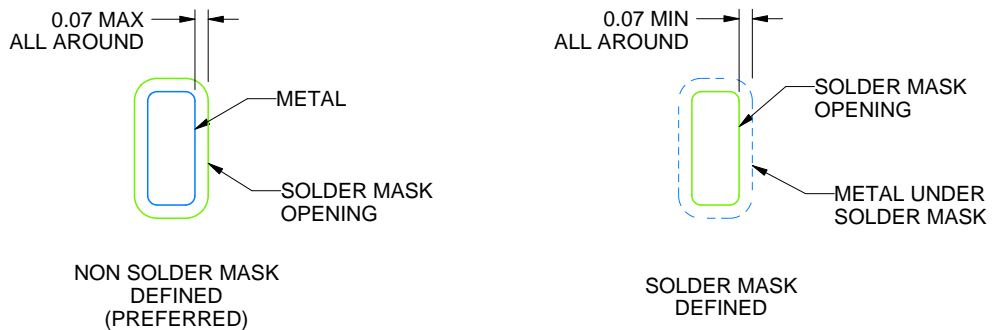
RHB0032E

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
SCALE:18X



SOLDER MASK DETAILS

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NOTES: (continued)

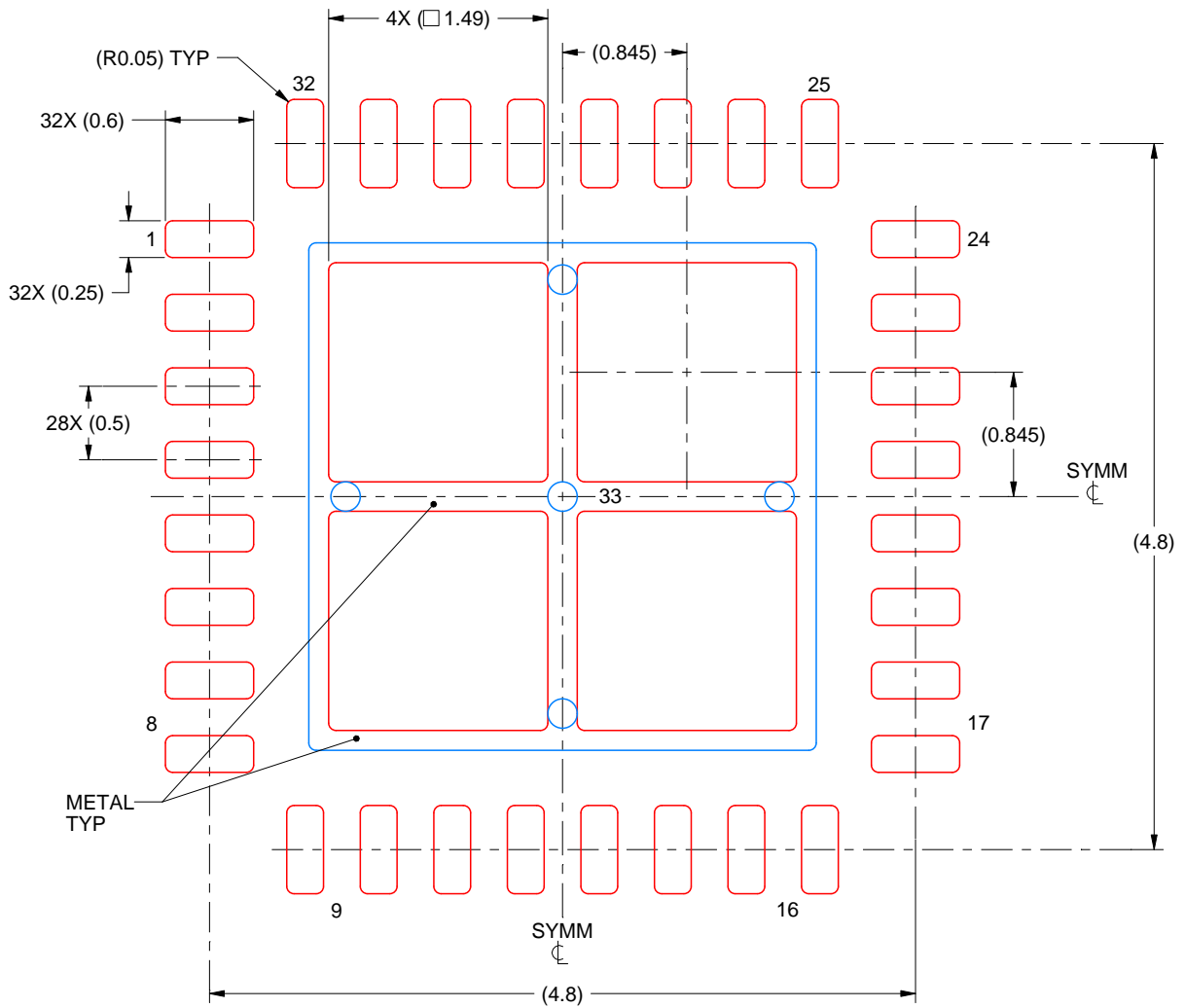
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RHB0032E

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 33:
 75% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
 SCALE:20X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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